Changing the Temperature in PSPICE Simulations

Overview

Circuit behavior often has strong temperature dependence. For example, in bipolar circuits the current depends on $I_S exp(V_{BE}/V_T)$ where the thermal voltage $V_T = k_B T/q$ (k_B = Boltzmann constant, T= absolute temperature and q=electronic charge). When the temperature changes, so does V_T . In addition, the scale current I_S depends on temperature. In PSPICE, for example, I_S is modeled as¹

EQ. 1

$$I_{s}(T) = I_{s}\left(\frac{T}{T_{\text{NOM}}}\right)^{X_{TI}} e^{\left((T/T_{\text{NOM}}-1)(E_{g}/V_{T})\right)}$$

where I_S is the scale current at the "nominal" temperature T_{NOM} (set at 300K by default)² and T is the operating temperature of the transistor (both in degrees Kelvin). Other parameters appear in EQ. 1 with values that are set in the •model statement for the particular type of transistor under consideration (for example, for the bipolar type Q2N2222, X_{TI} = 3 and E_{G} = 1.11V).

Next is a discussion of how to control temperature in PSPICE, including setting individual temperatures for each device in the circuit.

Setting T_{NOM}

The default value³ for parameter T_{NOM} is set by selecting PSPICE/EDIT PROFILE/SIMULATION SETTINGS and using the OPTIONS tab to get the menu in Figure 1.

Simulation Settings - BIAS									
General Analysis Include	e Files Libraries Stimulus Options D) ata Collect	ion Pi	robe Window					
Category:				(.OPTION)					
Analog Simulation	Relative accuracy of V's and I's:	0.001		(RELTOL)					
Gate-level Simulation	Best accuracy of voltages:	1.0u	volts	(VNTOL)					
Uutput file	Best accuracy of currents:	1.0p	amps	(ABSTOL)					
	0.01p	coulomb	s (CHGTOL)						
	Minimum conductance for any branch:	1.0E-12	1/ohm	(GMIN)					
	DC and bias "blind" iteration limit:	150		(ITL1)					
DC and bias "best guess" iteration limit: 20 (ITL2)									
Transient time point iteration limit: 10 (ITL4) Default nominal temperature: 30.0 *C (TNDM)									

FIGURE 1

Setting the value of T_{NOM}

Changing T_{NOM} results in a notation in the OUTPUT file as shown below:

*Analysis directives: •OP

¹ See the on-line PSPICE REFERENCE GUIDE, p. 212

² T_{NOM} is the temperature at which the model parameters have been fitted to get good *I-V* curves. ³ This value can be <u>overridden</u> by specifying the variable T_MEASURED in the •model statement of the device.

•TEMP 27 •OPTIONS TNOM= 30.0

The entry •OPTIONS TNOM= 30.0 shows that TNOM has been set to 30°C. The output file listing •TEMP 27 indicates that the <u>circuit</u> temperature is set at 27°C. In other words, the menu of Figure 1 and the variable T_{NOM} are about the selection of the <u>model</u> <u>parameters</u>, and have nothing to do with the <u>circuit</u> temperature.

It is recommended that you leave this menu at the default value 27° C because this is the temperature where the model parameters were set up.

Changing Circuit Temperature T

Simulation Settings - Transient
General Analysis Include Files Libraries Stimulus Options Data Collection Probe Window Analysis type: filme Domain (Transient) Options: General Settings Monte Carlo/Worst Case Parametric Sweep Save Bias Point Load Bias Point Carlo All Section (Sweep) Save Bias Point Cond Bias P
OK Cancel Apply Help

FIGURE 2

Menu for setting the circuit temperature (the "global" temperature) in the TRANSIENT simulation; in this case a request is made for <u>two</u> runs at the temperatures T=27°C and T=35°C.

The temperature of the entire circuit is set using the SIMULATION SETTINGS. For example, for a DC Bias simulation, we can follow the steps described by Herniter in his on-line supplement to his book. By selecting PSPICE/EDIT SIMULATION PROFILE and clicking on TEMPERATURE (SWEEP) we obtain the menu of Figure 2. In this menu, the temperature can be filled in, and checking the TEMPERATURE (SWEEP) box activates your choices. Changing the temperature leads to an entry in the OUTPUT FILE when the simulation is run like that below

*Analysis directives:

•OP

•TEMP 150

The line •TEMP sets the so-called "global temperature specification" of the simulation. That is, all the devices in the circuit are set to this temperature.

This approach works with other types of simulation as well. For example, for a TRANSIENT SIMULATION we can click on the ANALYSIS tab to obtain the menu shown in Figure 2. Here two temperatures have been selected, the default 27°C and also 35°C.

An example output waveform for a common emitter amplifier is shown in Figure 3. The corresponding added lines in the OUTPUT file are

- *Analysis directives:
- •TRAN/OP 0 2m 0 1u
- •TEMP 27 35

In addition, before the listing for each simulation the OUTPUT file lists the temperature as shown below for the 35°C run:



FIGURE 3

Example output waveform for two temperatures

Temperature adjusted •model parameters

If there are devices in your circuit, you can look at the •model parameters. For example, in the circuit of Figure 4 the temperature has been set using the menu of Figure 2 at $T=127^{\circ}C$. When the BIAS simulation is run, the output file shows the • model parameters of Figure 5.



FIGURE 4

Example current-mirror circuit where the temperature has been set at T = 127°C

Q2N	2222	ISE	1.43E-14	MJE	0.377	TR	4.69E-08
	NPN	NE	1.307	CJC	7.31E-12	ХТВ	1.5
IS	1.43E-14	BR	6.09E+00	MJC	0.3416	CN	2.42E+00
BF	255.9	NR	1	TF	4.11E-10	D	0.87
NF	1.00E+00	RB	10	XTF	3		
VAF	74.03	RC	1	VTF	1.70E+00		
IKF	0.2847	CJE	2.20E-11	ITE	0.6		

FIGURE 5

Output file listing of •model parameters for Figure 4 at T_{NOM}

However, in addition, the output file shows the <u>temperature-adjusted</u> model parameters of Figure 6. Note, in particular, that the scale current has changed in accord with EQ. 1, and that BF has changed as well. Most other parameters also have changed somewhat, indicating that the detailed temperature dependence is too complex for hand analysis.

Q2N2222		RB	10	IS	1.545E-09	VTF	1.7
		BR	9.377	ISS	0	ITF	0.6
BF	393.9	ISC	0	VJS	0.569	TR	4.691E-08
ISE	6.602E-11	VJC	0.569	CJS	0	XTB	1.5
VJE	0.569	CJC	8.008E-12	GAMMA	1E-11	CN	2.42
CJE	2.434E-11	RC	1	RCO	0	D	0.87
RE	0	RBM	10	VO	10		

FIGURE 6

Output file listing for temperature-adjusted •model parameters at T=127°C

Individual device temperatures

The above approach is fine if you want all the devices at the same temperature. However, in some circuits the operation is greatly affected when different devices have different temperatures. An example is the differential amplifier shown in Figure 7⁴. This circuit depends on both transistors being matched, that is, both having the same model parameters.

In Figure 7 the transistor temperatures relative to the global temperature are controlled by the parameters Q_TEMP1 and Q_TEMP2. As seen in Figure 7, both output voltages OUT1 and OUT2 are the same in this case where both transistors are at the same temperature. However, as shown in Figure 8, when the relative temperature of one transistor is increased relative to the global temperature by changing Q_TEMP2, the two outputs are no longer the same.

How is this individual control of temperatures accomplished?

- First a Q2N2222 is pasted on the schematic. By clicking on the transistor to highlight it and selecting EDIT/PSPICE MODEL we put it into the •model editor for this device.
- We copy the •model statement for the Q2N2222, and close the model editor. Delete the Q2N2222 transistor from the schematic.

⁴ The AC source plays no part in the Q-point simulation, so both bases are at DC ground in Figure 7 and Figure 8.

 Next, paste a BREAKOUT transistor QbreakN into the circuit⁵. QbreakN is a blank n-transistor, that is, a transistor with only default model parameters.



FIGURE 7

A differential amplifier allowing individual control of device temperatures; both transistors have the same temperature, 27°C



FIGURE 8

The same amplifier as Figure 7, but with transistor Q2 running 15°C hotter than Q1

⁵ The use of a breakout transistor allows us to choose our own name for the transistor model, which helps as a reminder several days or weeks from now in reconstructing what we did with this circuit.

📴 DIFFAMP.lib - PSpice Model Editor Lite - [Qbreakn]	
📴 Eile Edit View Model Plot Tools Window Help	_ 8 ×
	<u> 반</u> + 년 년
Models List 🗵 .model Qbreakn NPN	
Model Name Type Creation Da	
Qbreakn* BJT	v
Ready	

FIGURE 9

The listing for QbreakN as it is originally pasted onto the schematic

- Clicking on the transistor to highlight it and selecting EDIT/PSPICE MODEL we put this transistor into the •model editor as shown in Figure 9.
- . Next, we paste the copied •model statement for the Q2N2222 into the QbreakN window to make the QbreakN transistor the same as the Q2N2222. Then, just to keep track of the model, we change the name to Q TEMP1n.
- Next is the key step for temperature control: we specify the parameter T REL GLOBAL, which sets the device temperature relative to the global temperature. Normally this parameter has the default value of zero, but here we set it to a parameter Q TEMP1 that PSPICE can control directly, and we indicate that it is a parameter by enclosing {Q_TEMP1} in curly braces. See Figure 10.

DIFFAMP.lib) - PSpice M	lodel Editor Lite	e - [Q_TEMP1n]	
File Edit	View Model	l Plot Tools W	Window Help	_ 8 ;
0 🖻 🖬 🧉	j 🖪 🕺	• • • •		
1odels List		×	.model Q_TEMP1n NPN(Is=14.34f Xti=3 Eg=1.11 Vaf=74.03 Bf=255.9 Ne=1.307	
Model Name	Туре	Creation Date	+ Ise=14.34f Ikf=.2847 Xtb=1.5 Br=6.092 Nc=2 Isc=0 Ikr=0 Rc=1	
Q_TEMP2n	BJT		+ Cjc=7.306p Mjc=.3416 Vjc=.75 Fc=.5 Cje=22.01p Mje=.377 Vje=.75	
Q_TEMP1n	BJT		+ Tr=46.91n Tf=411.1p Itf=.6 Vtf=1.7 Xtf=3 Rb=10,T_REL_GLOBAL={Q_TEM	IP1})-
	Figu	RE 10		fi

The •model statement for the device Q TEMP1n setting the parameter T REL GLOBAL to {Q TEMP1}

The same procedure is used to set up another QbreakN, named Q_TEMP2n, as a Q2N2222 with T REL GLOBAL = {Q TEMP2}, a second temperature parameter. Now any type of simulation (BIAS, or TRANSIENT or whatever) can be run with these two device temperatures set as we wish relative to the global temperature. If we run the BIAS simulation for the case in Figure 8, we find in the OUTPUT file the listing in Figure 11 for the model parameters. The variables T Measured and T Current are identified in the next section. T Current does tell you the relative temperatures of the various devices in the circuit, but that aside, normally T Measured and T Current can be ignored.

	Q_TEMP1n	Q_TEMP2n
	NPN	NPN
T_Measured	27	27
T_Current	27	42
IS	1.43E-14	1.43E-14
BF	255.9	255.9
NF	1	1
VAF	74.03	74.03

FIGURE 11

Part of the BJT MODEL PARAMETERS listing for the simulation of Figure 8

Unlike the case using the menu of Figure 2, the output file for individually set temperatures does <u>not</u> list the temperature-adjusted •model parameters. The listing of temperature-adjusted parameters can be activated, however, by setting the device temperatures and <u>also</u> using Figure 2 to set the global temperature to a value <u>other than the default</u> value of 27°C, say to the value T=27.01°C. An example is shown in Figure 12. Comparison of BF and IS for the device at 27° C with Figure 5 shows they are nearly the same. Comparison of BF and IS for the device at 127° C with Figure 6 shows they also are close to the same.

	Q_TEMP1n	Q_TEMP2n	BR	6.092	9.378	ISS	0	0
			ISC	0	0	VJS	0.75	0.569
BF	255.9	393.9	VJC	0.75	0.569	CJS	0	0
ISE	1.436E-14	6.606E-11	CJC	7.306E-12	8.008E-12	GAMMA	1E-11	1E-11
VJE	0.75	0.569	RC	1	1	RCO	0	0
CJE	2.201E-11	2.434E-11	RBM	10	10	VO	10	10
RE	0	0	IS	1.436E-14	1.547E-09			
RB	10	10		-				

FIGURE 12

Temperature-adjusted parameters for two transistors, with Q_TEMP1n at 27.01°C (T_REL_GLOBAL=0) and Q_TEMP2n at 127.01°C (T_REL_GLOBAL=100) and the global temperature set using Figure 2 to T = 27.01°C.

Although we have changed the temperature for device Q2, the global temperature remains 27.01°C, as indicated in the OUTPUT file by the following line that appears before the listing of the simulated Q-point values:

**** OPERATING POINT INFORMATION TEMPERATURE = 27.010 DEG C

Again, you can keep track of what is happening by reading the OUTPUT file.

Summary

Just to summarize the many temperatures:

1. GLOBAL temperature = temperature of circuit as a whole. Set using PSPICE/EDIT SIMULATION PROFILE, and selecting the SIMULATION SETTINGS/ANALYSIS tab to obtain the TEMPERATURE (SWEEP) menu. Corresponds to the •TEMP <VALUE> command in the ANALYSIS DIRECTIVES of the OUTPUT FILE, and to the value listed as TEMPERATURE in the OUTPUT FILE.

2. T_REL_GLOBAL = temperature of device relative to the global (circuit) temperature. Set in the •model statement of the device by adding T_REL_GLOBAL= <VALUE>, where <VALUE> is the operating temperature of the device <u>relative to</u> the global temperature of the rest of the circuit. See the on-line Reference Manual, p. 51.

3. T_MEASURED = temperature where the device parameters were measured and fitted to *I-V* curves. Set in the •model statement of the device by adding the variable T_MEASURED = <VALUE>, where <VALUE> is the temperature you want. Normally should be left alone, at the default value of 27°C.

4. TNOM = <u>default</u> value of T_MEASURED. Set on the SIMULATIONS SETTINGS/ OPTION tab as T_{NOM} and overridden by T_MEASURED. Normally should be left alone, at the default value of 27°C. Corresponds to the •OPTIONS TNOM=<VALUE> command in the ANALYSIS DIRECTIVES of the OUTPUT FILE.

5. T_CURRENT = T_MEASURED+T_REL_GLOBAL. This temperature is listed in the output file, but has no bearing on the calculation. Don't worry about it.

Caution

It should be borne in mind that all transistor parameters vary from one device to another, and this is true of the parameters affecting the temperature dependence as well. Therefore, the PSPICE results for temperature dependence are only so-called "typical" results, and your results in the lab very likely will differ.